

Advanced Copper on Silicon Process Supported by Design Tools and Rapid Prototyping

ON Semiconductor introduces a new integrated passive device (IPD) process technology. An enhancement of the company's existing HighQ™ copper (Cu) on silicon (Si) IPD technology, the new IPD2 process features a second 5 um copper layer that increases inductor performance, allows greater flexibility and supports the design of highly precise, cost-effective IPDs for RF system in package applications in portable electronics equipment. One of the many manufacturing services offered by ON Semiconductor's custom Foundry Division, the HighQ IPD2 process utilizes advanced 8-inch wafer technology. Typical designs include baluns, low pass filters, band pass filters and diplexers used in the latest portable and wireless applications. Here, IPD2-based designs provide important benefits for circuit designers including reduced cost, reduced thickness, small footprint and higher performance that equates to longer battery life.

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